TEXAS INSTRUMENTS
SN74AHC132
JAJSQZ1K – MAY 1996 – REVISED FEBRUARY 2024

SN74AHC132 シュミット・トリガ入力付き、クワッド、正論理 NAND ゲート

1 特長

- 2V～5.5V の V_{CC} で動作
- 非常に低速な入力遷移からの動作
- 温度補償スレッショルド レベル
- 高いノイズ耐性
- SNx4AHC00 と同じピン配置
- JESD 17 準拠で
  250mA 超のラッチアップ性能
- JESD 22 を上回る ESD 保護
  - 人体モデルで 2000V
  - 荷電デバイス モデルで 1000V

2 アプリケーション

- 電子 POS
- 通信インフラ
- ネットワーク・スイッチ
- 試験および測定

3 概要

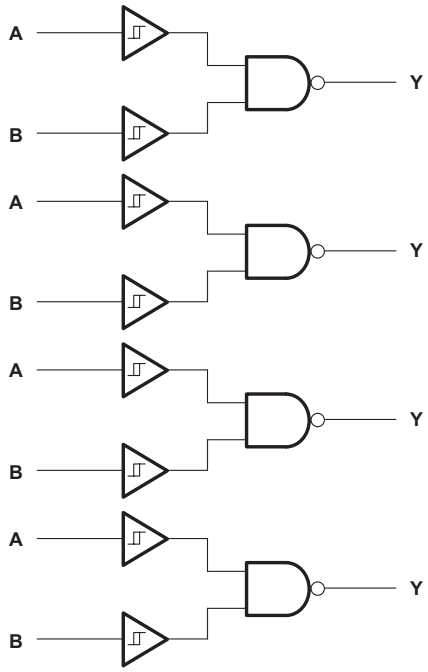
SN7AHC132 デバイスは 4 チャネルの正論理 NAND ゲートで、2V～5.5V の V_{CC} で動作するように設計されています。このデバイスはブール関数
$Y = \overline{A \times B}$ または $Y = \overline{A} + \overline{B}$ を正論理で実行します。

シュミット トリガ入力により、ノイズ耐性が向上し、低速な入力信号遷移がサポートされます。

パッケージ情報

部品番号	パッケージ (1)	パッケージ サイズ(2)	本体サイズ (3)
SN7AHC132	BQA (WQFN、14)	3mm × 2.5mm	3mm × 2.5mm
	D (SOIC、14)	8.65mm × 6mm	8.65mm × 3.9mm
	DB (SSOP、14)	6.2mm × 7.8mm	6.2mm × 5.3mm
	DGV (TVSOP、14)	3.6mm × 6.4mm	3.6mm × 4.4mm
	PW (TSSOP、14)	5mm × 6.4mm	5mm × 4.4mm
	RGY (VQFN、14)	3.5mm × 3.5mm	3.5mm × 3.5mm
	N (PDIP、14)	19.3mm × 9.4mm	19.3mm × 6.35mm
	NS (SOP、14)	10.2mm × 7.8mm	5.3mm × 10.3mm

(1) 詳細については、セクション 11 を参照してください。
(2) パッケージ サイズ (長さ×幅) は公称値であり、該当する場合はピンも含まれます
(3) 本体サイズ (長さ×幅) は公称値であり、ピンは含まれません。



概略回路図

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4 Pin Configuration and Functions

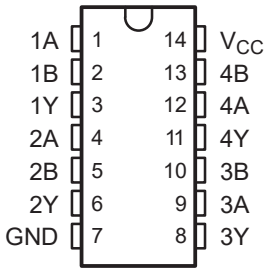


図 4-1. SN74AHC132 D, DB, DGV, N, NS, or PW Package, 14-Pin (Top View)

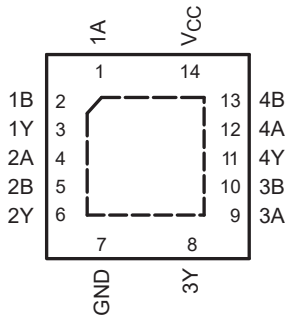


図 4-2. SN74AHC132 RGY Package, 14-Pin VQFN (Top View)

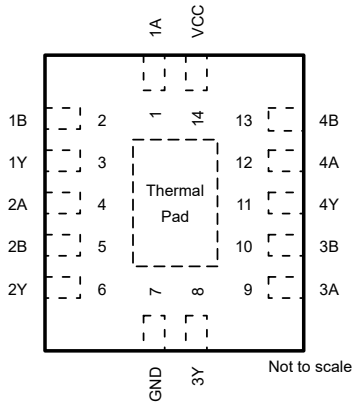


図 4-3. SN74AHC132 BQA Package, 14-Pin WQFN (Top View)

表 4-1. Pin Functions

PIN		TYPE[1]	DESCRIPTION
NAME	NO.		
1A	1	I	1A Input
1B	2	I	1B Input
1Y	3	O	1Y Output
2A	4	I	2A Input
2B	5	I	2B Input
2Y	6	O	2Y Output
3Y	8	O	3Y Output
3A	9	I	3A Input
3B	10	I	3B Input
4Y	11	O	4Y Output
4A	12	I	4A Input
4B	13	I	4B Input
GND	7	—	Ground Pin
V_{CC}	14	—	Power Pin
Thermal Pad[2]		—	The thermal pad can be connected to GND or left floating. Do not connect to any other signal or supply.

(1) I = input, O = output
(2) For BQA only.

5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage range		–0.5	7	V
V_I	Input voltage range(2)		–0.5	7	V
V_O	Output voltage range(2)		–0.5	V_{CC} + 0.5	V
I_{IK}	Input clamp current	V_I < 0		–20	mA
I_{OK}	Output clamp current	V_O < 0 or V_O > V_{CC}		±20	mA
I_O	Continuous output current	V_O = 0 to V_{CC}		±25	mA
	Continuous current through V_{CC} or GND			±50	mA

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

5.2 Handling Ratings

			MIN	MAX	UNIT
T_{stg}	Storage temperature range		–65	150	°C
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins(1)	0	2000	V
		Charged device model (CDM), per JEDEC specification JESD22-C101, all pins(2)	0	1000	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)(1)

			SN74AHC132		UNIT
			MIN	MAX	
V_{CC}	Supply voltage		2	5.5	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2 V		–50	µA
		V_{CC} = 3.3 V ± 0.3 V		–4	mA
		V_{CC} = 5 V ± 0.5 V		–8	
I_{OL}	Low-level output current	V_{CC} = 2 V		50	µA
		V_{CC} = 3.3 V ± 0.3 V		4	mA
		V_{CC} = 5 V ± 0.5 V		8	
T_A	Operating free-air temperature		–40	125	°C

(1) All unused inputs of the device must be held at V_{CC} or GND for proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs* (SCBA004).

5.4 Thermal Information

THERMAL METRIC[1]		SN74AHC132								UNIT
		BQA	D	DB	DR	N	NS	PW	RGY	
		14 PINS								
$R_{\theta JA}$	Junction-to-ambient thermal resistance	88.3	124.6	107.1	90.6	57.4	90.7	147.7	57.5	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	90.9	79.7	59.6	50.9	44.9	48.3	77.4	57.5	
$R_{\theta JB}$	Junction-to-board thermal resistance	56.8	81.2	54.4	44.8	37.2	49.4	90.9	33.6	
ψ_{JT}	Junction-to-top characterization parameter	9.9	39.3	20.5	14.7	30.1	14.6	27.2	3.4	
ψ_{JB}	Junction-to-board characterization parameter	56.7	80.8	53.8	44.5	37.1	49.1	90.2	33.7	
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	33.4	N/A	N/A	N/A	N/A	N/A	N/A	13.9	

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report (SPRA953).

5.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}	T_A = 25°C			SN74AHC132		–40°C to 125°C SN74AHC132		UNIT
			MIN	TYP	MAX	MIN	MAX	MIN	MAX	
V_{T+} Positive-going input threshold voltage		3 V	1.2		2.2	1.2	2.2	1.2	2.2	V
		4.5 V	1.75		3.15	1.75	3.15	1.75	3.15	
		5.5 V	2.15		3.85	2.15	3.85	2.15	3.85	
$V_{T–}$ Negative-going input threshold voltage		3 V	0.9		1.9	0.9	1.9	0.9	1.9	V
		4.5 V	1.35		2.75	1.35	2.75	1.35	2.75	
		5.5 V	1.65		3.35	1.65	3.35	1.65	3.35	
ΔV_T Hysteresis ($V_{T+} – V_{T–}$)		3 V	0.3		1.2	0.3	1.2	0.3	1.2	V
		4.5 V	0.4		1.4	0.4	1.4	0.4	1.4	
		5.5 V	0.5		1.6	0.5	1.6	0.5	1.6	
V_{OH}	I_{OH} = –50 µA	2 V	1.9	2		1.9		1.9		V
		3 V	2.9	3		2.9		2.9		
		4.5 V	4.4	4.5		4.4		4.4		
	I_{OH} = –4 mA	3 V	2.58			2.48		2.48		
	I_{OH} = –8 mA	4.5 V	3.94			3.8		3.8		
V_{OL}	I_{OL} = 50 µA	2 V			0.1		0.1		0.1	V
		3 V			0.1		0.1		0.1	
		4.5 V			0.1		0.1		0.1	
	I_{OL} = 4 mA	3 V			0.36		0.44		0.44	
	I_{OL} = 8 mA	4.5 V			0.36		0.44		0.44	
I_I	V_I = 5.5 V or GND	0 V to 5.5 V			±0.1		±1		±1	µA
I_{CC}	$V_I = V_{CC}$ or GND, I_O = 0	5.5 V			2		20		20	µA
C_i	$V_I = V_{CC}$ or GND	5 V		1.9	10		10		10	pF

5.6 Switching Characteristics, V_{CC} = 3.3 V ± 0.3 V

over recommended operating free-air temperature range (unless otherwise noted) (see (1))

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T_A = 25°C			SN74AHC132		T_A = –40°C to 125°C SN74AHC132		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{PLH}	A or B	Y	C_L = 15 pF		5.6(1)	11.9(1)	1	14	1	15	ns
t_{PHL}					5.6(1)	11.9(1)	1	14	1	15	
t_{PLH}	A or B	Y	C_L = 50 pF		7.6	15.4	1	17.5	1	19	ns
t_{PHL}					7.6	15.4	1	17.5	1	19	

(1) On products compliant to MIL-PRF-38535, this parameter is not production tested.

5.7 Switching Characteristics, V_{CC} = 5 V ± 0.5 V

over recommended operating free-air temperature range (unless otherwise noted) (see (1))

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T_A = 25°C			SN74AHC132		T_A = –40°C to 125°C SN74AHC132		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{PLH}	A or B	Y	C_L = 15 pF		3.9(1)	7.7(1)	1	9	1	10	ns
t_{PHL}					3.9(1)	7.7(1)	1	9	1	10	
t_{PLH}	A or B	Y	C_L = 50 pF		5.3	9.7	1	11	1	12	ns
t_{PHL}					5.3	9.7	1	11	1	12	

(1) On products compliant to MIL-PRF-38535, this parameter is not production tested.

5.8 Noise Characteristics

V_{CC} = 5 V, C_L = 50 pF, T_A = 25°C(1)

PARAMETER		SN74AHC132			UNIT
		MIN	TYP	MAX	
$V_{OL(P)}$	Quiet output, maximum dynamic V_{OL}		0.45	0.8	V
$V_{OL(V)}$	Quiet output, minimum dynamic V_{OL}		–0.35	–0.8	V
$V_{OH(V)}$	Quiet output, minimum dynamic V_{OH}		4.8		V
$V_{IH(D)}$	High-level dynamic input voltage	3.5			V
$V_{IL(D)}$	Low-level dynamic input voltage			1.5	V

(1) Characteristics are for surface-mount packages only.

5.9 Operating Characteristics

V_{CC} = 5 V, T_A = 25°C

PARAMETER		TEST CONDITIONS		TYP	UNIT
C_{pd}	Power dissipation capacitance	No load,	f = 1 MHz	11	pF

5.10 Typical Characteristics

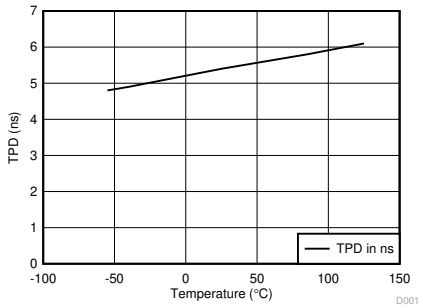


図 5-1. TPD vs Temperature

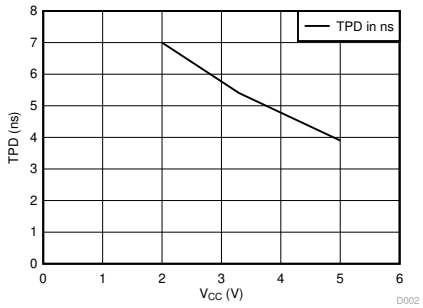
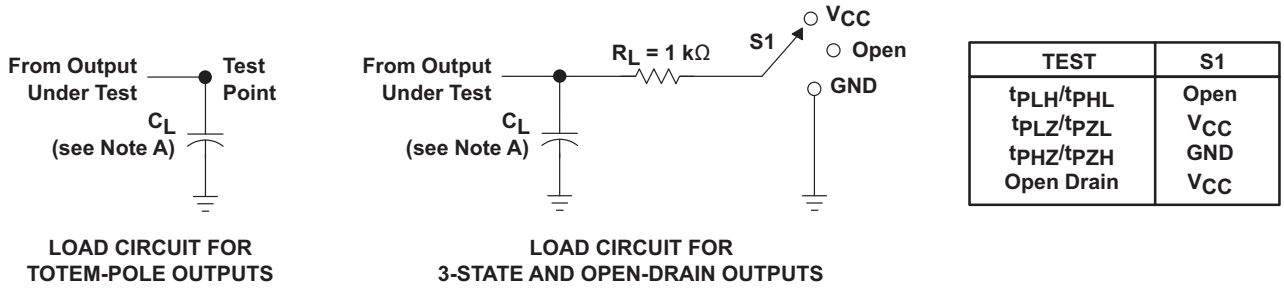


図 5-2. TPD vs V_{CC}

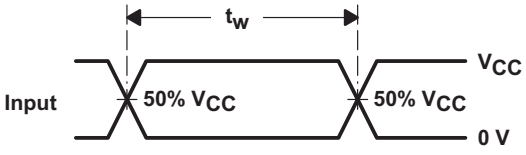
6 Parameter Measurement Information



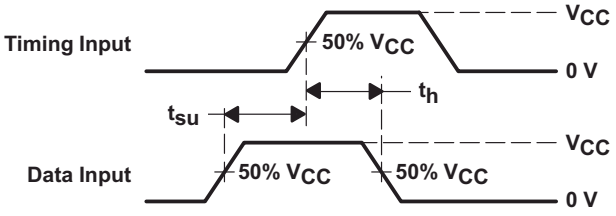
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_{CC}
t_{PHZ}/t_{PZH}	GND
Open Drain	V_{CC}

LOAD CIRCUIT FOR TOTEM-POLE OUTPUTS

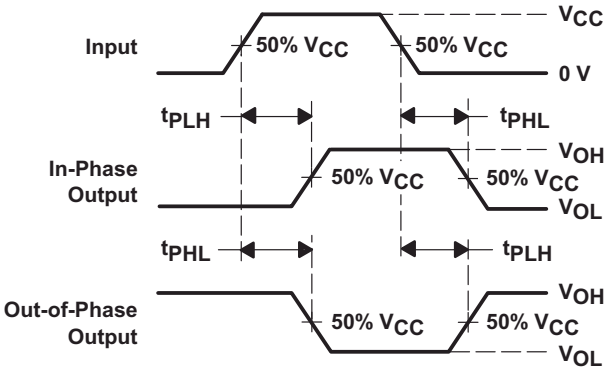
LOAD CIRCUIT FOR 3-STATE AND OPEN-DRAIN OUTPUTS



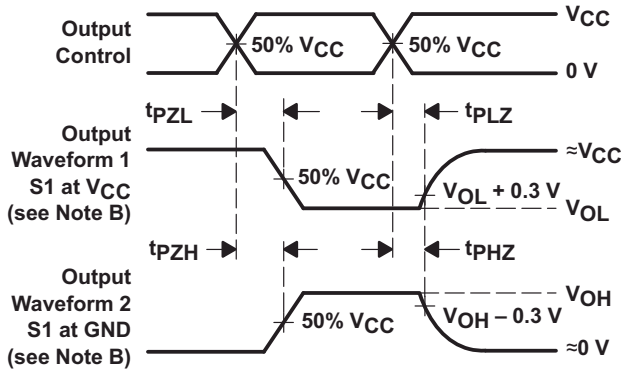
VOLTAGE WAVEFORMS PULSE DURATION



VOLTAGE WAVEFORMS SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS PROPAGATION DELAY TIMES INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS ENABLE AND DISABLE TIMES LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 1 MHz, Z_O = 50 Ω, t_r ≤ 3 ns, t_f ≤ 3 ns.
D. The outputs are measured one at a time with one input transition per measurement.
E. All parameters and waveforms are not applicable to all devices.

図 6-1. Load Circuit and Voltage Waveforms

7 Detailed Description

7.1 Overview

The SN74AHC132 is a quadruple 2-input positive-NAND gate with low drive that produces slow rise and fall times. This reduces ringing on the output signal.

Each circuit functions as a NAND gate, but because of the Schmitt action, it has different input threshold levels for positive- and negative-going signals.

These circuits are temperature compensated and can be triggered from the slowest of input ramps and still give clean, jitter-free output signals.

7.2 Functional Block Diagram

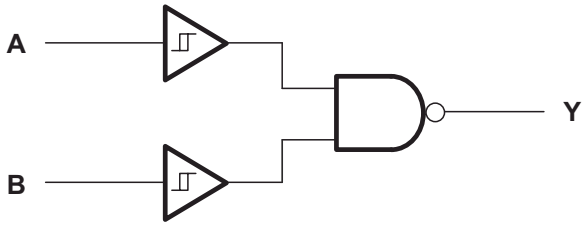


図 7-1. Logic Diagram, Each Gate (Positive Logic)

7.3 Feature Description

- Wide operating voltage range
  - Operates from 2 V to 5.5 V
- Allows down voltage translation
  - Inputs accept voltages to 5.5 V

7.4 Device Functional Modes

表 7-1. Function Table (Each Gate)

INPUTS		OUTPUT Y
A	B	
H	H	L
L	X	H
X	L	H

8 Application and Implementation

注

以下のアプリケーション情報は、TI の製品仕様に含まれるものではなく、TI ではその正確性または完全性を保証いたしません。個々の目的に対する製品の適合性については、お客様の責任で判断していただくことになります。お客様は自身の設計実装を検証しテストすることで、システムの機能を確認する必要があります。

8.1 Application Information

The SN74AHC132 is a low-drive CMOS device that can be used for a multitude of bus interface type applications where output ringing is a concern. The low drive and slow edge rates will minimize overshoot and undershoot on the outputs. The inputs can accept voltages to 5.5 V at any valid V_{CC}, thus making the device an excellent choice for down translation.

8.2 Typical Application

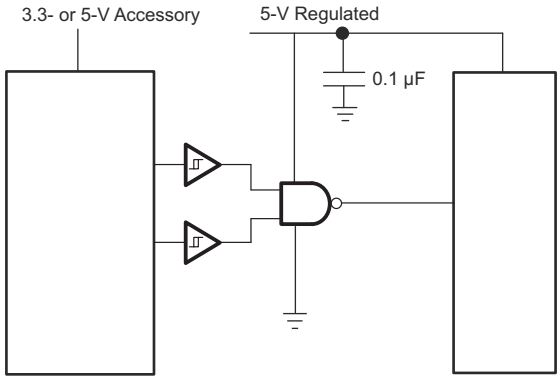


図 8-1. Typical Application Schematic

8.2.1 Design Requirements

This device uses CMOS technology and has balanced output drive. Take care to avoid bus contention because it can drive currents that would exceed maximum limits. The high drive will also create fast edges into light loads, so routing and load conditions should be considered to prevent ringing.

8.2.2 Detailed Design Procedure

1. Recommended input conditions:
   - For rise time and fall time specifications, see Δt/ΔV in the *Recommended Operating Conditions* table.
   - For specified high and low levels, see V_{IH} and V_{IL} in the *Recommended Operating Conditions* table.
   - Inputs are overvoltage tolerant allowing them to go as high as 5.5 V at any valid V_{CC}.
2. Recommend output conditions:
   - Load currents should not exceed 25 mA per output and 50 mA total for the part.
   - Outputs should not be pulled above V_{CC}.

8.2.3 Application Curves

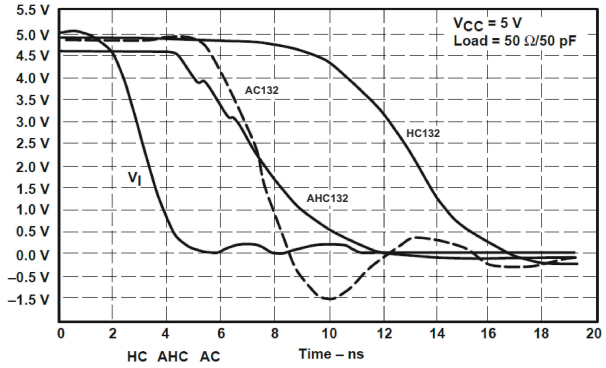


図 8-2. Switching Characteristics Comparison

8.3 Power Supply Recommendations

The power supply can be any voltage between the MIN and MAX supply-voltage rating located in the *Recommended Operating Conditions* table.

Each V_{CC} pin should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, 0.1µF is recommended. If there are multiple V_{CC} pins, then a 0.01 µF or a 0.022 µF is recommended for each power pin. It is acceptable to parallel multiple bypass capacitors to reject different frequencies of noise. A 0.1 µF and a 1 µF are commonly used in parallel. Install the bypass capacitor as close to the power pin as possible for best results.

8.4 Layout

8.4.1 Layout Guidelines

When using multiple bit logic devices, inputs should not float. In many cases, functions or parts of functions of digital logic devices are unused. Some examples are when only two inputs of a triple-input AND gate are used, or when only 3 of the 4-buffer gates are used. Such input pins should not be left unconnected because the undefined voltages at the outside connections result in undefined operational states.

Specified in the *Layout Examples* are rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that should be applied to any particular unused input depends on the function of the device. Generally they will be tied to GND or V_{CC}, whichever makes more sense or is more convenient. It is acceptable to float outputs unless the part is a transceiver. If the transceiver has an output enable pin, then it will disable the outputs section of the part when asserted. This will not disable the input section of the I/Os so they also cannot float when disabled.

8.4.2 Layout Example

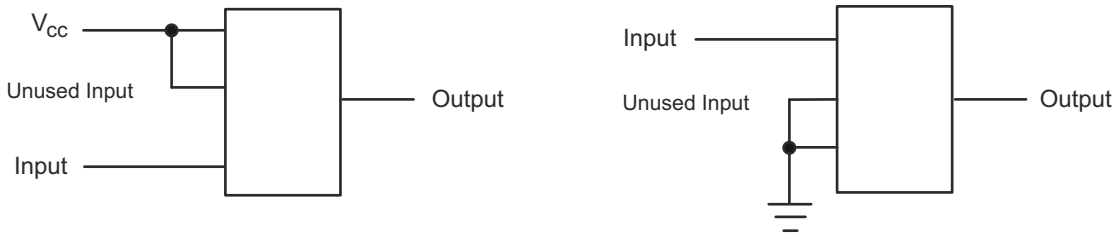


図 8-3. Layout Diagram

9 Device and Documentation Support

9.1 Documentation Support (Analog)

9.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, *CMOS Power Consumption and Cpd Calculation* application note
- Texas Instruments, *Designing With Logic* application note
- Texas Instruments, *Thermal Characteristics of Standard Linear and Logic (SLL) Packages and Devices* application note
- Texas Instruments, *Implications of Slow or Floating CMOS Inputs* application note

9.2 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、www.tij.co.jp のデバイス製品フォルダを開いてください。[通知] をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取ることができます。 変更の詳細については、改訂されたドキュメントに含まれている改訂履歴をご覧ください。

9.3 サポート・リソース

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9.4 Trademarks

テキサス・インスツルメンツ E2E™ is a trademark of Texas Instruments.
すべての商標は、それぞれの所有者に帰属します。

9.5 静電気放電に関する注意事項

この IC は、ESD によって破損する可能性があります。テキサス・インスツルメンツは、IC を取り扱う際には常に適切な注意を払うことを推奨します。正しい取り扱いおよび設置手順に従わない場合、デバイスを破損するおそれがあります。

ESD による破損は、わずかな性能低下からデバイスの完全な故障まで多岐にわたります。精密な IC の場合、パラメータがわずかに変化するだけで公表されている仕様から外れる可能性があるため、破損が発生しやすくなっています。

9.6 用語集

テキサス・インスツルメンツ用語集　　この用語集には、用語や略語の一覧および定義が記載されています。

10 Revision History

Changes from Revision J (October 2023) to Revision K (February 2024)	Page
• 「特長」からマシン モデルを削除	1
• Updated thermal values for D package from RθJA = 90.6 to 124.6, RθJC(top) = 50.9 to 79.7, RθJB = 44.8 to 81.2, ΨJT = 14.7 to 39.3, ΨJB = 44.5 to 80.8, RθJC(bot) = N/A, all values in °C/W	5

Changes from Revision I (August 2023) to Revision J (October 2023)	Page
• Updated thermal values for PW package from RθJA = 122.6 to 147.7, RθJC(top) = 51.4 to 77.4, RθJB = 64.4 to 90.9, ΨJT = 6.7 to 27.2, ΨJB = 63.8 to 90.2, all values in °C/W	5

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74AHC132BQAR	ACTIVE	WQFN	BQA	14	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AHC132	Samples
SN74AHC132DBR	ACTIVE	SSOP	DB	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HA132	Samples
SN74AHC132DGVR	ACTIVE	TVSOP	DGV	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HA132	Samples
SN74AHC132DR	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AHC132	Samples
SN74AHC132N	ACTIVE	PDIP	N	14	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-40 to 125	SN74AHC132N	Samples
SN74AHC132NSR	ACTIVE	SO	NS	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AHC132	Samples
SN74AHC132PWR	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU | SN	Level-1-260C-UNLIM	-40 to 125	HA132	Samples
SN74AHC132RGYR	ACTIVE	VQFN	RGY	14	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	HA132	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

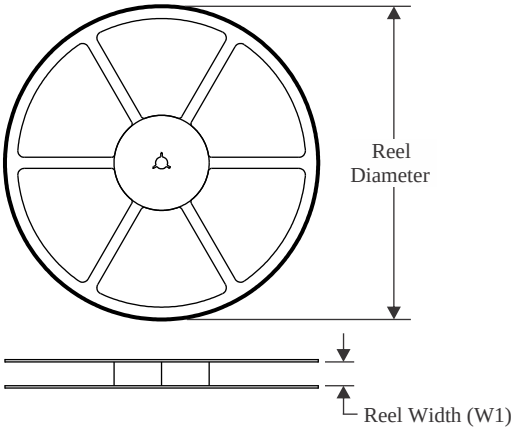
(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

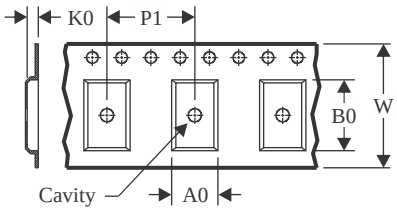
(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

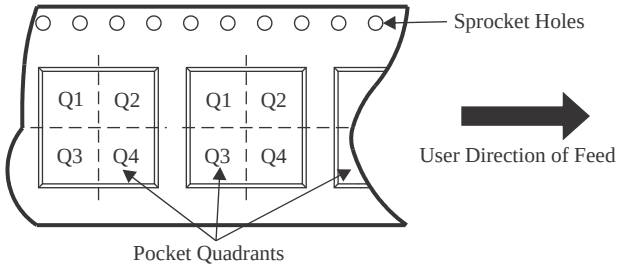


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

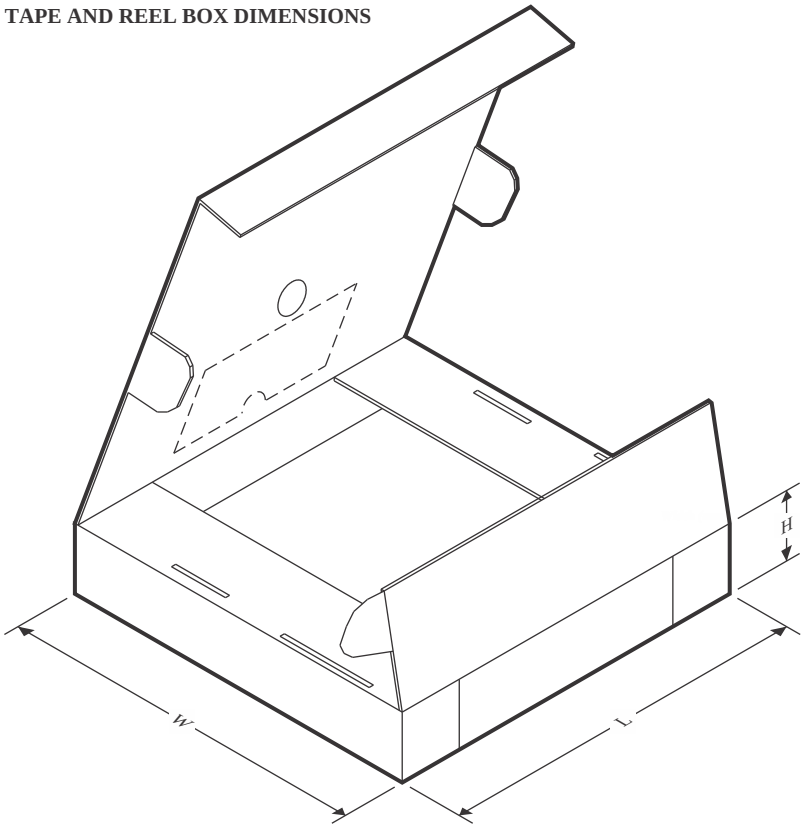
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74AHC132BQAR	WQFN	BQA	14	3000	180.0	12.4	2.8	3.3	1.1	4.0	12.0	Q1
SN74AHC132DBR	SSOP	DB	14	2000	330.0	16.4	8.35	6.6	2.4	12.0	16.0	Q1
SN74AHC132DGVR	TVSOP	DGV	14	2000	330.0	12.4	6.8	4.0	1.6	8.0	12.0	Q1
SN74AHC132DR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
SN74AHC132NSR	SO	NS	14	2000	330.0	16.4	8.2	10.5	2.5	12.0	16.0	Q1
SN74AHC132PWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74AHC132PWR	TSSOP	PW	14	2000	330.0	12.4	6.85	5.45	1.6	8.0	12.0	Q1
SN74AHC132PWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74AHC132RGYR	VQFN	RGY	14	3000	330.0	12.4	3.75	3.75	1.15	8.0	12.0	Q1

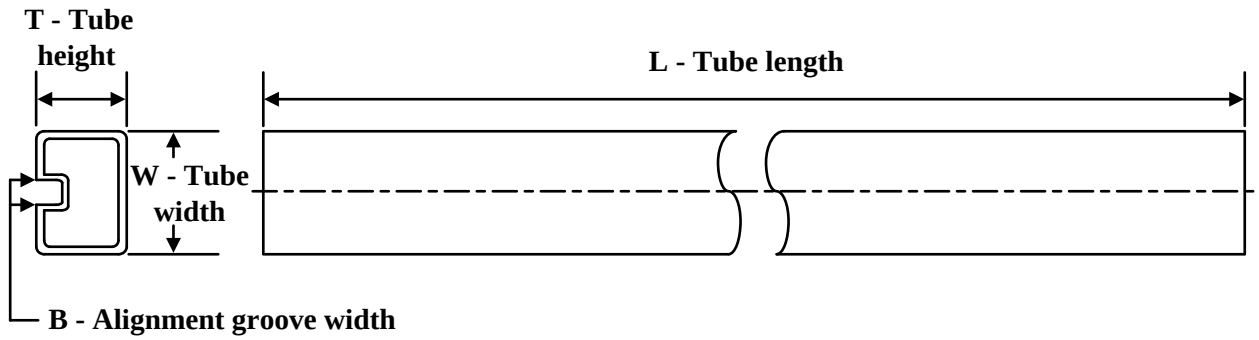
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74AHC132BQAR	WQFN	BQA	14	3000	210.0	185.0	35.0
SN74AHC132DBR	SSOP	DB	14	2000	356.0	356.0	35.0
SN74AHC132DGVR	TVSOP	DGV	14	2000	356.0	356.0	35.0
SN74AHC132DR	SOIC	D	14	2500	356.0	356.0	35.0
SN74AHC132NSR	SO	NS	14	2000	356.0	356.0	35.0
SN74AHC132PWR	TSSOP	PW	14	2000	356.0	356.0	35.0
SN74AHC132PWR	TSSOP	PW	14	2000	366.0	364.0	50.0
SN74AHC132PWR	TSSOP	PW	14	2000	353.0	353.0	32.0
SN74AHC132RGYR	VQFN	RGY	14	3000	356.0	356.0	35.0

TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
SN74AHC132N	N	PDIP	14	25	506	13.97	11230	4.32
SN74AHC132N	N	PDIP	14	25	506	13.97	11230	4.32

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